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C I E N T & T R A D E M A R K S

Substitute for form 1449A-140

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet	1	of	1	Attorney Docket Number	NTI-019-5-1D
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U.S. PATENT DOCUMENTS

Examiner Initials*	Cited No. ¹	Document Number Number - Kind Code ^{2/3 known}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear
PD	A01	US-6,610,989	B1	08/26/2003	Takahashi
	A02	US-6,370,441	B1	04/09/2002	Ohnuma
	A03	US-6,145,118		11/07/2000	Tomita
	A04	US-6,067,375		05/23/2000	Tsudaka
	A05	US-6,058,203		05/02/2000	Tsudaka
	A06	US-6,042,257		03/28/2000	Tsudaka
	A07	US-5,885,748		03/23/1999	Ohnuma
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Examiner Initials*	Cite No. ¹	Foreign Patent Document Cntry Code ³ Number ⁴ Kind Code ⁵ ^(if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear	T ⁶

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER SIGNATURE: *Paul Dinh* DATE CONSIDERED: *2/21/01*

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INFORMATION DISCLOSURE CITATION PTO-1449		ATTY. DOCKET NO. NTI-019-5-1D		SERIAL NO. <u>10/688559</u> Filed Herewith		
		APPLICANT Pierrat, et al.				
		FILING DATE <u>10/16/03</u> Filed Herewith		GROUP <u>2825</u>		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<u>PD</u>	4,231,811	11/4/80	Somekh, et al.	148	1.5	9/13/79
	4,456,371	6/26/84	Lin	355	71	6/30/82
	4,902,899	2/20/90	Lin, et al.	250	492.1	6/1/87
	5,498,579	3/12/96	Borodovsky, et al.	437	250	6/8/94
	5,553,274	9/3/96	Liebmann	395	500	6/6/95
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	5,663,017	9/2/97	Schinella, et al.	430	5	6/7/95
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	6,077,310	6/20/00	Yamamoto, et al.	716	19	1/29/99
<u>PD</u>	6,078,738	6/20/00	Garza, et al.	395	500.22	5/8/97
EXAMINER	<u>Paul. Dinh</u>		DATE CONSIDERED	<u>2/21/06</u>		

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		Filing Date <u>10/16/03</u>	Group <u>2825</u>
		Filed Herewith	

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	5,208,124	5/4/1993	Sporon-Fiedler, et al.	430	5	3/19/1991
	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
	5,958,635	9/28/1999	Reich, et al.	430	30	10/20/1997
	5,972,541	10/26/1999	Sugasawara, et al.	430	5	3/4/1998
	6,007,310	12/28/1999	Jacobsen, et al.	417	362	5/23/1997
	6,114,071	9/5/2000	Chen, et al.	430	5	4/6/1998
	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
PD	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

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		Filing Date <i>10/16/03</i>	Group <i>2825</i>
		Filed Herewith	

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<i>PD</i>	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
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<i>PD</i>	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
<i>PD</i>	6,453,457 B1	9/17/2002	Pierrat, et al.	716	19	9/29/2000
<i>PD</i>	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	5	3/15/2002

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PTO-1449		Applicant PIERRAT, Christophe	Filed Herewith
		Filing Date <i>10/16/03</i>	Group <i>2825</i>
		Filed Herewith	

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	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998

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6,453,457	09-2002	Pierrat et al.	716	19
<i>PD</i> 6,523,162	02-2003	Agrawal et al.	716	19

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SUMMARY		Applicant PIERRAT, Christophe	Filing Date 10/16/03 Group 2825 Filed Herewith

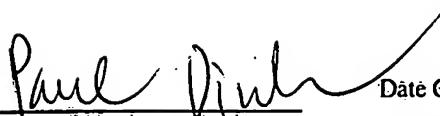
FOREIGN PATENT DOCUMENTS

Ref ID	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
00076	WO 00/67074 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
00077	WO 00/67075 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
00078	WO 00/67076 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>

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		Applicant PIERRAT, Christophe					
		Filing Date <i>10/16/03</i>	Group <i>2825</i>				
		Filed Herewith					
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						<input type="checkbox"/>	<input type="checkbox"/>
<i>PP</i>	3-80525	4/5/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
<i>PP</i>	2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
<i>PD</i>	WO 99/47981	9/23/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>

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Date Considered:

2/21/06

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00150	Wiley, J., et al., "Device Yield and Reliability by Specification of Mask Defects", Solid State Technology, Vol. 36, No. 7, pp. 65-66, 70, 72, 74, 77, July 1993.		
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	APPLICANT Pierrat, et al.	
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	APPLICANT Pierrat, et al. <i>10/16/07</i>	GROUP <i>2825</i>
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EXAMINER <i>Paul Dinkin</i>	DATE CONSIDERED	<i>2/21/06</i>

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
<i>PD</i>	Choi, Y., et al., "Optical Proximity Correction on Attenuated Phase Shifting Photo Mask for Dense Contact Array", LG Semicon Company (11 pages).		
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EXAMINER: *Paul Dink* Date Considered: *2/21/04*

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-019-5-1D Applicant PIERRAT, Christophe Filing Date <u>10/16/03</u> Group <u>2825</u> Filed Herewith	Serial No. <u>10/688559</u> Filed Herewith
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
<u>PI</u>	Balasinski, A., et al., "Comparison of Mask Writing Tools and Mask Simulations for 0.16um Devices", IEEE, SEMI Advanced Semiconductor Manufacturing Conference, pp. 372-377 (1999).		

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Paul Dink

Date Considered:

2/21/06

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
PI	Chuang, H., et al., "Practical Applications of 2-D Optical Proximity Corrections for Enhanced Performance of 0.25um Random Logic Devices", IEEE, pp. 18.7.1-18.7.4, December 1997.		

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Paul Miller

Date Considered:

2/21/05

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
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<u>PD</u>	Cobb, N., et al., "Fast, Low-Complexity Mask Design", SPIE, Vol. 2440, pp. 313-327, February 22-24, 1995.		
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EXAMINER:

Paul Dink

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